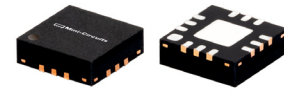


# Ultra High Dynamic Range, Shutdown Monolithic Amplifier

## TSS-13LN+

50Ω      1MHz to 1 GHz



CASE STYLE: DQ1225

### The Big Deal

- Ultra-High IP3, +39.2 dBm typ.
- Low supply voltage, 3 to 5V
- Excellent Noise Figure, 1.1 dB typ.
- Shutdown feature

### Product Overview

TSS-13LN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-13LN+ has good input and output return loss over a broad frequency range. TSS-13LN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

### Key Features

Feature	Advantages
Broad Band: 1MHz to 1GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular
Extremely High IP3 38.4 dBm typical at 1 MHz 39.2 dBm typical at 0.5 GHz	The TSS-13LN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 11-18 dB above the P1dB point. This feature makes this amplifier ideal for use in: <ul style="list-style-type: none"><li>• Driver amplifiers for complex waveform up converter paths</li><li>• Drivers in linearized transmit systems</li><li>• Secondary amplifiers in ultra-High Dynamic range receivers</li></ul>
Shutdown feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage to minimize DC power consumption
Low Noise Figure 1.1 dB at 0.5 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range
Low Supply Voltage	TSS-13LN+ supports low supply voltage operation which indicate low power consumption.



# Ultra High Dynamic Range, Shutdown Monolithic Amplifier

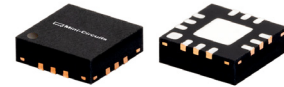
1 MHz to 1 GHz

## Product Features

- High IP3, 39.2 dBm typ. at 0.5 GHz
- Gain, 22.8 dB typ. at 0.5 GHz
- Low noise figure, 1.1 dB at 0.5 GHz
- Low voltage, 5V and 3V
- Shutdown feature

## Typical Applications

- Base station infrastructure
- CATV
- Cellular



Generic photo used for illustration purposes only

## TSS-13LN+

CASE STYLE: DQ1225

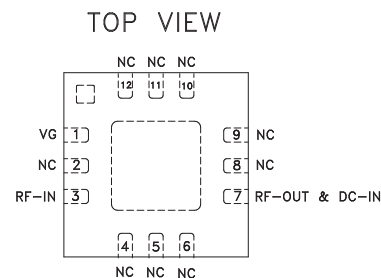
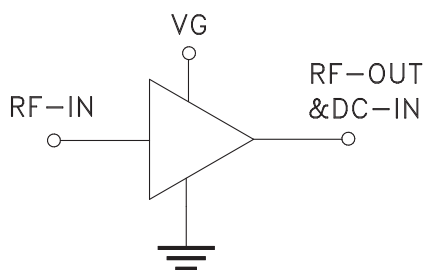
**+RoHS Compliant**

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

## General Description

TSS-13LN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-13LN+ has good input and output return loss over a broad frequency range. TSS-13LN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

### simplified schematic and pad description



Function	Pin Number	Description
RF IN	3	RF Input
RF-OUT and DC-IN	7	RF Output and DC Bias
GND	Paddle	Connections to ground.
NC	2, 4-6, 8-12	No connection, grounded externally
VG	1	Control voltage for shutdown (VG)

Electrical Specifications<sup>1</sup> at 25°C & 50Ω, unless noted

Parameter	Condition (MHz)	Amplifier-ON			Amplifier-OFF	Amplifier-ON	Amplifier-OFF	Units
		VDD = 5V			VDD = 5V	VDD = 3V	VDD = 3V	
		Min.	Typ.	Max.	Typ.	Typ.	Typ.	
Frequency Range		1		1000	1-1000	1-1000	1-1000	MHz
Noise Figure	1		3.1			3.0		dB
	20		1.1			1.1		
	250		1.1			1.1		
	500		1.1			1.1		
	1000		1.2			1.3		
Gain	1	22.1	24.7	27.1	-24	23.9	-24	dB
	20	—	24.2	—	-22	23.5	-22	
	250	20.6	23.0	25.2	-21	22.3	-21	
	500	—	22.8	—	-22	21.9	-22	
	1000	18.2	20.9	22.2	-27	19.5	-27	
Reversed Isolation	1-1000		26		27	26	27	dB
Input Return Loss	1		11		12	10	12	dB
	20		15		12	15	12	
	250		18		12	19	12	
	500		21		12	17	12	
	1000		14		10	10	10	
Output Return Loss	1		11		1	11	1	dB
	20		19		2	21	2	
	250		18		2	21	2	
	500		25		2	21	2	
	1000		11		2	10	2	
Output Power @ 1dB compression AMP-ON	1		20.3			14.2		dBm
	20		22.4			16.3		
	250		24.1			19.3		
	500		24.5			19.5		
	1000		23.4			18.3		
Output IP3 (Pout = 0dBm/Tone)	1	—	38.4			31.6		dBm
	20	—	40.3			33.2		
	250	—	39.6			34.4		
	500	35.4	39.2			33		
	1000	—	36.2			29.4		
Device Operating Voltage (VDD)		4.75	5	5.25	5	3	3	V
Device Operating Current (ID)			142	151	5	72	3	mA
Control Voltage (VG)			0		5	0	5	V
DC Current (ID) Variation Vs. Temperature <sup>2</sup>			10			33		uA/degC
DC Current(ID) Variation Vs. Voltage			0.025			0.033		mA/mV

1. Measured on Mini-Circuits Characterization test board TB-TSS-13LN+. See Characterization Test Circuit (Fig. 1)

2. (Current at 105°C — Current at -45°C)/150

Absolute Maximum Ratings<sup>3</sup>

Parameter	Ratings
Operating Temperature (ground lead)	-40°C to 105°C
Storage Temperature	-65°C to 150°C
Total Power Dissipation	3.3W
Input Power	28 dBm (5 minutes max.) 6 dBm (continuous) for 1- 30 MHz 10 dBm (continuous) for 0.03-1 GHz
DC Voltage V <sub>DD</sub> <sup>4</sup> (Pad 7)	10V
DC Voltage V <sub>G</sub> <sup>5</sup> (Pad 1)	10V

<sup>3</sup> Permanent damage may occur if these limits are exceeded.

<sup>4</sup> Measured by keeping V<sub>G</sub>=0V.

<sup>5</sup> Measured by keeping V<sub>DD</sub>=5V.

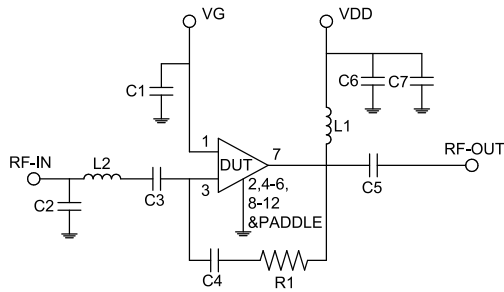
Control Voltage (V<sub>G</sub>) Fig. 1

	Min.	Typ.	Max.	Units
Amplifier-ON	—	0	0.7	V
Amplifier-OFF	1.9	5	—	V

Switching Specifications

Parameter		5V Typ.	3V Typ.	Units
Amplifier ON to Shutdown	OFF TIME (50% Control to 10% RF)	4.8	6.2	μs
	FALL TIME (90 to 10% RF)	7.4	3.6	
Amplifier Shutdown to ON	ON TIME (50% Control to 90% RF)	95.2	144.7	μs
	RISE TIME (10% to 90% RF)	60.0	200.7	
Control Voltage Leakage		482.9	311.0	mV

Characterization Test Circuit / Recommended Application Circuit



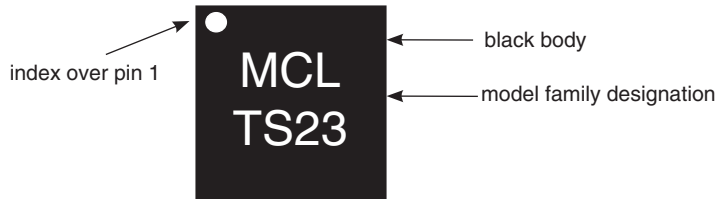
Component	Size	Value	Part Number	Manufacturer
C1	0402	0.1uF	GRM155R71C104KA88D	Murata
C2	0402	1.5pF	GRM1555C1H1R5CA1D	Murata
C3	0603	2.2uF	GRM188C71E225KE11D	Murata
C4	0402	0.1uF	GRM155R71C104KA88D	Murata
C5	0603	2.2uF	GRM188C71E225KE11D	Murata
C6	0402	1000pF	GRM1555C1H102JA01D	Murata
C7	0805	10uF	GRM21BC71E106KE11L	Murata
L1	1210	15uH	LQH32DN150K53L	Murata
L2	0603	5.1nH	0603CS-5N1XJLU	Coilcraft
R1	0402	1.5KOhm	RK73H1ETTP1501F	Koa

Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-TSS-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB) , output IP3 (OIP3) and noise figure measured using Agilent’s N5242A PNA-X microwave network analyzer.

Conditions:

- Gain and Return Loss: Pin= -25dBm
- Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +0dBm/tone at output.
- Switching Time  
 RF Signal: Pin=-25 dBm, f<sub>RF</sub>=500 MHz.  
 V<sub>DD</sub>=3 & 5V DC, V<sub>G</sub>=Pulse signal at 1 KHz with V<sub>HIGH</sub>=5V, V<sub>LOW</sub>=0V, 50% duty cycle.

Product Marking



Marking may contain other features or characters for internal lot control